

# Wenchao Chen

## List of Publications by Year in descending order

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57  
papers

2,989  
citations

471509

17  
h-index

206112

48  
g-index

57  
all docs

57  
docs citations

57  
times ranked

5772  
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomically thin p-n junctions with van der Waals heterointerfaces. <i>Nature Nanotechnology</i> , 2014, 9, 676-681.	31.5	1,953
2	18.5% efficient graphene/GaAs van der Waals heterostructure solar cell. <i>Nano Energy</i> , 2015, 16, 310-319.	16.0	180
3	Observation of ballistic avalanche phenomena in nanoscale vertical InSe/BP heterostructures. <i>Nature Nanotechnology</i> , 2019, 14, 217-222.	31.5	153
4	Tuning of the Contact Properties for High-Efficiency Si/PEDOT:PSS Heterojunction Solar Cells. <i>ACS Energy Letters</i> , 2017, 2, 556-562.	17.4	75
5	Highly efficient graphene-on-gap modulator by employing the hybrid plasmonic effect. <i>Optics Letters</i> , 2017, 42, 1736.	3.3	44
6	Electrothermal Characterization of Single-Walled Carbon Nanotube (SWCNT) Interconnect Arrays. <i>IEEE Nanotechnology Magazine</i> , 2009, 8, 718-728.	2.0	43
7	Tunable THz Multiband Frequency-Selective Surface Based on Hybrid Metal-Graphene Structures. <i>IEEE Nanotechnology Magazine</i> , 2017, 16, 1132-1137.	2.0	41
8	Wideband Modeling of Graphene-Based Structures at Different Temperatures Using Hybrid FDTD Method. <i>IEEE Nanotechnology Magazine</i> , 2015, 14, 250-258.	2.0	30
9	Electrothermal Cosimulation of 3-D Carbon-Based Heterogeneous Interconnects. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2016, 6, 518-526.	2.5	30
10	Fully Coupled Multiphysics Simulation of Crosstalk Effect in Bipolar Resistive Random Access Memory. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 3647-3653.	3.0	29
11	Electrothermal Characterization in 3-D Resistive Random Access Memory Arrays. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 4720-4728.	3.0	28
12	Electrothermal Effects on Hot-Carrier Reliability in SOI MOSFETs under AC Versus Circuit-Speed Random Stress. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 3669-3676.	3.0	24
13	Optical Kerr effect and third harmonic generation in topological Dirac/Weyl semimetal. <i>Optics Express</i> , 2019, 27, 38270.	3.4	24
14	ZnO, GaN, and InN Functionalized Nanowires for Sensing and Photonics Applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 1092-1101.	2.9	22
15	Study on High-Density Integration Resistive Random Access Memory Array From Multiphysics Perspective by Parallel Computing. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 1747-1753.	3.0	21
16	Electrothermal Effects on Hot Carrier Injection in n-Type SOI FinFET Under Circuit-Speed Bias. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 3802-3807.	3.0	18
17	Broadband Janus Scattering from Tilted Dipolar Metagratings. <i>Laser and Photonics Reviews</i> , 2022, 16, .	8.7	18
18	Effect of Nano-Porosity on High Gain Permeable Metal-Base Transistors. <i>Advanced Functional Materials</i> , 2014, 24, 6056-6065.	14.9	17

#	ARTICLE	IF	CITATIONS
19	Carrier dynamics and design optimization of electrolyte-induced inversion layer carbon nanotube-silicon Schottky junction solar cell. Applied Physics Letters, 2012, 100, 103503.	3.3	15
20	Electrothermal Investigation on Vertically Aligned Single-Walled Carbon Nanotube Contacted Phase-Change Memory Array for 3-D ICs. IEEE Transactions on Electron Devices, 2015, 62, 3258-3263.	3.0	15
21	Modeling and simulation of graphene-gated graphene-GaAs Schottky junction field-effect solar cell for its performance enhancement. IEEE Transactions on Electron Devices, 2015, 62, 3760-3766.	3.0	15
22	Computational study of graphene-based vertical field effect transistor. Journal of Applied Physics, 2013, 113, 094507.	2.5	13
23	Intrinsic delay of permeable base transistor. Journal of Applied Physics, 2014, 116, .	2.5	13
24	Scaling Analysis of High Gain Monolayer MoS <sub>2</sub> Photodetector for Its Performance Optimization. IEEE Transactions on Electron Devices, 2016, 63, 1608-1614.	3.0	12
25	Massively Parallel Electromagnetic-Thermal Cosimulation of Large Antenna Arrays. IEEE Antennas and Wireless Propagation Letters, 2020, 19, 1551-1555.	4.0	12
26	Electrical-Thermal Cosimulation of Coaxial TSVs With Temperature-Dependent MOS Effect Using Equivalent Circuit Models. IEEE Transactions on Electromagnetic Compatibility, 2020, 62, 2247-2256.	2.2	12
27	Modeling and simulation of carbon nanotube-semiconductor heterojunction vertical field effect transistors. Journal of Applied Physics, 2013, 113, .	2.5	11
28	Fully Coupled Electrothermal Simulation of Large RRAM Arrays in the "Thermal-House". IEEE Access, 2019, 7, 3897-3908.	4.2	11
29	Modeling and Simulation of Resistive Random Access Memory With Graphene Electrode. IEEE Transactions on Electron Devices, 2020, 67, 915-921.	3.0	11
30	Performance analysis of carbon nanotube contacted phase change memory by finite element method. Journal of Applied Physics, 2011, 110, .	2.5	10
31	Design Considerations for Si- and Ge-Stacked Nanosheet pMOSFETs Based on Quantum Transport Simulations. IEEE Transactions on Electron Devices, 2020, 67, 26-32.	3.0	10
32	An Improved Algorithm for Drift Diffusion Transport and Its Application on Large Scale Parallel Simulation of Resistive Random Access Memory Arrays. IEEE Access, 2019, 7, 31273-31285.	4.2	9
33	An Active Absorber Based on Nonvolatile Floating-Gate Graphene Structure. IEEE Nanotechnology Magazine, 2017, 16, 189-195.	2.0	8
34	Parallel Simulation of Fully Coupled Electrothermal Processes in Large-Scale Phase-Change Memory Arrays. IEEE Transactions on Electron Devices, 2019, 66, 5117-5125.	3.0	8
35	Quantum Transport Study of Si Ultrathin-Body Double-Gate pMOSFETs: $\langle I \rangle$ and $\langle I^2 \rangle$ vs. $V_g$ and $V_d$ . IEEE Transactions on Electron Devices, 2019, 66, 655-663.	3.0	7
36	Terahertz frequency selective surface based on metal-graphene structure with independent frequency tuneability. IET Microwaves, Antennas and Propagation, 2019, 13, 911-916.	1.4	6

#	ARTICLE	IF	CITATIONS
37	Magnetic Metamirrors as Spatial Frequency Filters. IEEE Transactions on Antennas and Propagation, 2020, 68, 5505-5511.	5.1	6
38	Diffusion Barrier Prediction of Graphene and Boron Nitride for Copper Interconnects by Deep Learning. IEEE Access, 2020, 8, 210542-210549.	4.2	5
39	An Artificial Neural Network Model for Electro-Thermal Effect Affected Hot Carrier Injection Reliability in 14-nm FinFETs. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 4827-4834.	4.6	5
40	A Hybrid Streamline Upwind Finite Volume-Finite Element Method for Semiconductor Continuity Equations. IEEE Transactions on Electron Devices, 2021, 68, 5421-5429.	3.0	4
41	Carrier Dynamics of Nanopillar Textured Ultrathin Si Film/PEDOT:PSS Heterojunction Solar Cell. IEEE Journal of Photovoltaics, 2018, 8, 757-762.	2.5	3
42	Recent progress of nano-electromagnetic compatibility (nano-EMC) in the emerging carbon nanoelectronics. IEEE Electromagnetic Compatibility Magazine, 2018, 7, 71-81.	0.1	3
43	Fully coupled electrothermal simulation of resistive random access memory (RRAM) array. Science China Information Sciences, 2020, 63, 1.	4.3	3
44	Multiphysics Computation for Resistive Random Access Memories With Different Metal Oxides. IEEE Transactions on Electron Devices, 2022, 69, 133-140.	3.0	3
45	Hexahedron-Based Control Volume Finite Element Method for Fully Coupled Nonlinear Drift-Diffusion Transport Equations in Semiconductor Devices. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 2965-2978.	4.6	3
46	First-principles investigation of copper diffusion barrier performance in defective 2D layered materials*. Nanotechnology, 2022, 33, 165201.	2.6	2
47	Electrothermal characterization of SOI FinFETs. , 2016, , .		1
48	Modeling and simulation of Si/PEDOT:PSS planar heterojunction photovoltaics by finite element method. , 2017, , .		1
49	Multiphysics Modeling and Simulation of Carrier Dynamics and Thermal Transport in Monolayer MoS <sub>2</sub> /WSe <sub>2</sub> Heterojunction. IEEE Transactions on Electron Devices, 2018, 65, 4542-4547.	3.0	1
50	Rigorous Modeling and Investigation of Low-Field Hole Mobility in Silicon and Germanium Gate-All-Around Nanosheet Transistors. IEEE Transactions on Electron Devices, 2022, 69, 4777-4785.	3.0	1
51	Modelling of multilayer graphene (MLG)-based structures at different temperatures. , 2015, , .		0
52	Multiphysics modeling and simulation of ultra-thin channel Germanium on insulator (GeOI) MOSFETs. , 2017, , .		0
53	An improved multifilamentary conduction model for multiphysics analysis of reset process in resistive random access memory. AIP Advances, 2019, 9, 045310.	1.3	0
54	Electrothermal Study on Resistive Random Access Memory (RRAM) Arrays. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
55	Electrothermal Effects on Reliability of Vertical Resistive Random Access Memory Array by Parallel Computing. , 2019, , .		0
56	Electrothermal Modeling and Simulation of Resistive Random Access Memory (RRAM) with Different Resistive Switching Oxides. , 2020, , .		0
57	A Physics-based Compact Model for Set Process of Resistive Random Access Memory (RRAM) with Graphene Electrode. , 2022, , .		0